



### STL19N65M5 Information



For Reference Only

Part Number STL19N65M5

Manufacturer STMicroelectronics

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 650V 12.5A POWERFLAT

Package 4-PowerFlat? HV

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# **Certified Quality**

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## STL19N65M5 Specifications

Manufacturer Part NumberSTL19N65M5ManufacturerSTMicroelectronicsCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackage4-PowerFlat? HVSeriesMDmesh? VFET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)650VCurrent - Continuous Drain (Id) @ 25°C2.3A (Ta), 12.5A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250µAGate Charge (Qg) (Max) @ Vgs31nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1240pF @ 100VVgs (Max)±25VFET Feature-Power Dissipation (Max)2.8W (Ta), 90W (Tc)Rds On (Max) @ Id, Vgs24000 (Max) @ 7.5A, 10V		
Category  Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single  Package  4-PowerFlat? HV  Series  MDmesh? V  FET Type  N-Channel  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Discrete Semiconductor Products  Transistors - FETs, MOSFETs - Single  4-PowerFlat? HV  MDmesh? V  MDmesh? V  4-PowerFlat? HV  N-Channel  500  500  500  100  100  100  100  10	Manufacturer Part Number	STL19N65M5
Transistors - FETs, MOSFETs - Single         Package       4-PowerFlat? HV         Series       MDmesh? V         FET Type       N-Channel         Technology       MOSFET (Metal Oxide)         Drain to Source Voltage (Vdss)       650V         Current - Continuous Drain (Id) @ 25°C       2.3A (Ta), 12.5A (Tc)         Drive Voltage (Max Rds On, Min Rds On)       10V         Vgs(th) (Max) @ Id       5V @ 250μA         Gate Charge (Qg) (Max) @ Vgs       31nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       1240pF @ 100V         Vgs (Max)       ±25V         FET Feature       -         Power Dissipation (Max)       2.8W (Ta), 90W (Tc)         Rds On (Max) @ Id, Vgs       240 mOhm @ 7.5A, 10V	Manufacturer	STMicroelectronics
Package       4-PowerFlat? HV         Series       MDmesh? V         FET Type       N-Channel         Technology       MOSFET (Metal Oxide)         Drain to Source Voltage (Vdss)       650V         Current - Continuous Drain (Id) @ 25°C       2.3A (Ta), 12.5A (Tc)         Drive Voltage (Max Rds On, Min Rds On)       10V         Vgs(th) (Max) @ Id       5V @ 250μA         Gate Charge (Qg) (Max) @ Vgs       31nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       1240pF @ 100V         Vgs (Max)       ±25V         FET Feature       -         Power Dissipation (Max)       2.8W (Ta), 90W (Tc)         Rds On (Max) @ Id, Vgs       240 mOhm @ 7.5A, 10V	Category	Discrete Semiconductor Products
Series         MDmesh? V           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         650V           Current - Continuous Drain (Id) @ 25°C         2.3A (Ta), 12.5A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         31nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1240pF @ 100V           Vgs (Max)         ±25V           FET Feature         -           Power Dissipation (Max)         2.8W (Ta), 90W (Tc)           Rds On (Max) @ Id, Vgs         240 mOhm @ 7.5A, 10V		Transistors - FETs, MOSFETs - Single
FET Type  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  N-Channel  10V  2.3A (Ta), 12.5A (Tc)  10V  10V  2.50µA  31nC @ 10V  1240pF @ 100V  2.5V  FET Feature	Package	4-PowerFlat? HV
Technology  Drain to Source Voltage (Vdss)  650V  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  MOSFET (Metal Oxide)  650V  2.3A (Ta), 12.5A (Tc)  10V  5V @ 250μA  31nC @ 10V  1240pF @ 100V  1240pF @ 100V  2.5V  FET Feature  -  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  2.8W (Ta), 90W (Tc)  Rds On (Max) @ Id, Vgs	Series	MDmesh? V
Drain to Source Voltage (Vdss)       650V         Current - Continuous Drain (Id) @ 25°C       2.3A (Ta), 12.5A (Tc)         Drive Voltage (Max Rds On, Min Rds On)       10V         Vgs(th) (Max) @ Id       5V @ 250μA         Gate Charge (Qg) (Max) @ Vgs       31nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       1240pF @ 100V         Vgs (Max)       ±25V         FET Feature       -         Power Dissipation (Max)       2.8W (Ta), 90W (Tc)         Rds On (Max) @ Id, Vgs       240 mOhm @ 7.5A, 10V	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Sty @ 250µA  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  2.3A (Ta), 12.5A (Tc)  2.3A (Ta), 12.5A (Tc)  2.3A (Ta), 12.5A (Tc)  2.5V  5V @ 250µA  1240pF @ 100V  1240pF @ 100V  2.5V  2.5V  FET Feature	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)       10V         Vgs(th) (Max) @ Id       5V @ 250μA         Gate Charge (Qg) (Max) @ Vgs       31nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       1240pF @ 100V         Vgs (Max)       ±25V         FET Feature       -         Power Dissipation (Max)       2.8W (Ta), 90W (Tc)         Rds On (Max) @ Id, Vgs       240 mOhm @ 7.5A, 10V	Drain to Source Voltage (Vdss)	650V
Vgs(th) (Max) @ Id       5V @ 250μA         Gate Charge (Qg) (Max) @ Vgs       31nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       1240pF @ 100V         Vgs (Max)       ±25V         FET Feature       -         Power Dissipation (Max)       2.8W (Ta), 90W (Tc)         Rds On (Max) @ Id, Vgs       240 mOhm @ 7.5A, 10V	Current - Continuous Drain (Id) @ 25°C	2.3A (Ta), 12.5A (Tc)
Gate Charge (Qg) (Max) @ Vgs       31nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       1240pF @ 100V         Vgs (Max)       ±25V         FET Feature       -         Power Dissipation (Max)       2.8W (Ta), 90W (Tc)         Rds On (Max) @ Id, Vgs       240 mOhm @ 7.5A, 10V	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds       1240pF @ 100V         Vgs (Max)       ±25V         FET Feature       -         Power Dissipation (Max)       2.8W (Ta), 90W (Tc)         Rds On (Max) @ Id, Vgs       240 mOhm @ 7.5A, 10V	Vgs(th) (Max) @ Id	5V @ 250μA
Vgs (Max)         ±25V           FET Feature         -           Power Dissipation (Max)         2.8W (Ta), 90W (Tc)           Rds On (Max) @ Id, Vgs         240 mOhm @ 7.5A, 10V	Gate Charge (Qg) (Max) @ Vgs	31nC @ 10V
FET Feature - Power Dissipation (Max) 2.8W (Ta), 90W (Tc) Rds On (Max) @ Id, Vgs 240 mOhm @ 7.5A, 10V	Input Capacitance (Ciss) (Max) @ Vds	1240pF @ 100V
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  2.8W (Ta), 90W (Tc)  240 mOhm @ 7.5A, 10V	Vgs (Max)	±25V
Rds On (Max) @ Id, Vgs 240 mOhm @ 7.5A, 10V	FET Feature	-
	Power Dissipation (Max)	2.8W (Ta), 90W (Tc)
	Rds On (Max) @ Id, Vgs	240 mOhm @ 7.5A, 10V
Operating Temperature 150°C (TJ)	Operating Temperature	150°C (TJ)
Mounting Type Surface Mount	Mounting Type	Surface Mount
Supplier Device Package PowerFlat? (8x8) HV	Supplier Device Package	PowerFlat? (8x8) HV
Package / Case 4-PowerFlat? HV	Package / Case	4-PowerFlat? HV
Report errors?		Report errors?

### STL19N65M5 Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### STL19N65M5 Payment Methods



















## STL19N65M5 Shipping Methods













If you have any question about STL19N65M5, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com